



STB155N3LH6 STD155N3LH6

N-channel 30 V, 2.4 mΩ, 80 A, D²PAK, DPAK
STripFET™VI DeepGATE™ Power MOSFET

Features

Order codes	V _{DSS}	R _{DS(on)} max	I _D ⁽¹⁾	P _{TOT}
STB155N3LH6	30 V	3.0 mΩ	80 A	110 W
STD155N3LH6				

1. Current limited by package

- 100% avalanche tested
- Logic level drive

Applications

- Switching applications
- Automotive

Description

These devices are N-channel Power MOSFETs developed using the 6th generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFETs exhibits the lowest R_{DS(on)} in all packages.

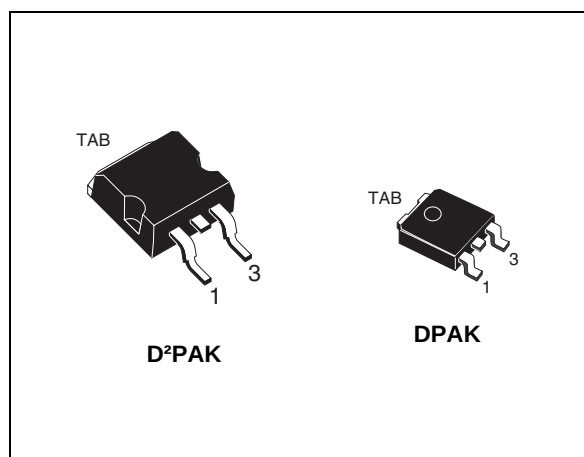
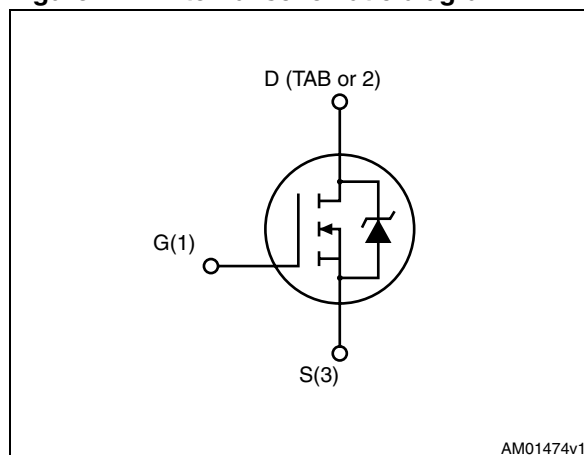


Figure 1. Internal schematic diagram



AM01474v1

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB155N3LH6	155N3LH6	D ² PAK	Tape and reel
STD155N3LH6		DPAK	

Contents

1 **Electrical ratings** 3

2 **Electrical characteristics** 4

 2.1 Electrical characteristics (curves) 6

3 **Test circuits** 8

4 **Package mechanical data** 9

5 **Packaging mechanical data** 14

6 **Revision history** 17



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	80	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		$^\circ\text{C}$

1. Limited by wire bonding.

2. Pulse width limited by safe operating area.

Table 3. Thermal resistance

Symbol	Parameter	Value		Unit
		D ² PAK	DPAK	
$R_{thj-case}$	Thermal resistance junction-case max	1.36		$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	35	50	$^\circ\text{C/W}$

1. When mounted on 1 inch² OZ Cu board.

Table 4. Thermal resistance

Symbol	Parameter	Value	Unit
I_{AV}	Not-repetitive avalanche current	40	A
$E_{AS}^{(1)}$	Single pulse avalanche energy	525	mJ

1. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 40\text{ A}$, $V_{DD} = 25\text{ V}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified).

Table 5. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 250\text{ }\mu\text{A}$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 30\text{ V}$ $V_{DS} = 30\text{ V}, T_c = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}, I_D = 40\text{ A}$		2.4	3.0	m Ω
		$V_{GS} = 5\text{ V}, I_D = 40\text{ A}$		3.2	4.0	m Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	3800	-	pF
C_{oss}	Output capacitance			725		pF
C_{rss}	Reverse transfer capacitance			420		pF
Q_g	Total gate charge	$V_{DD} = 15\text{ V}, I_D = 80\text{ A}$	-	80	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{ V}$		15		nC
Q_{gd}	Gate-drain charge	(see Figure 14)		15		nC
R_G	Gate input resistance	f = 1 MHz gate bias Bias = 0 test signal level = 20 mV open drain	-	1.5	-	Ω

Table 7. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 15)	-	15 85	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 15)	-	100 40	-	ns ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		80 320	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40\text{ A}$, $V_{GS} = 0$	-		1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 24\text{ V}$ (see Figure 17)	-	35 26.5 1.7		ns nC A

1. Pulse width limited by safe operating area.

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

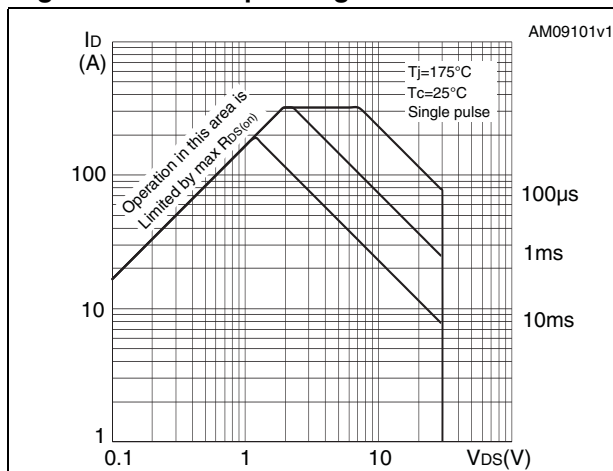


Figure 3. Thermal impedance

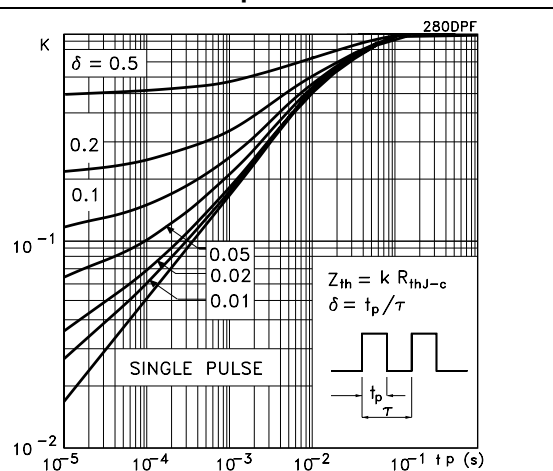


Figure 4. Output characteristics

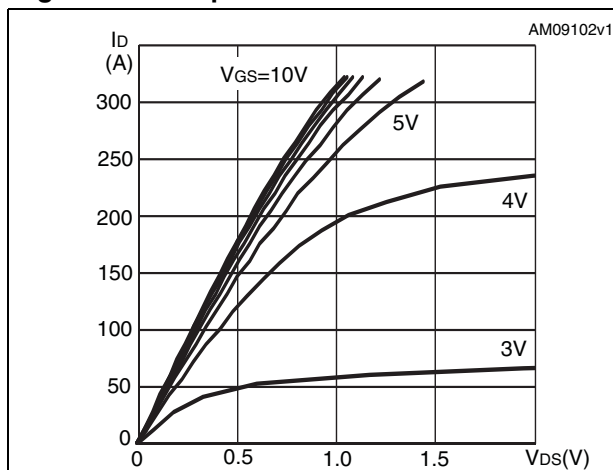


Figure 5. Transfer characteristics

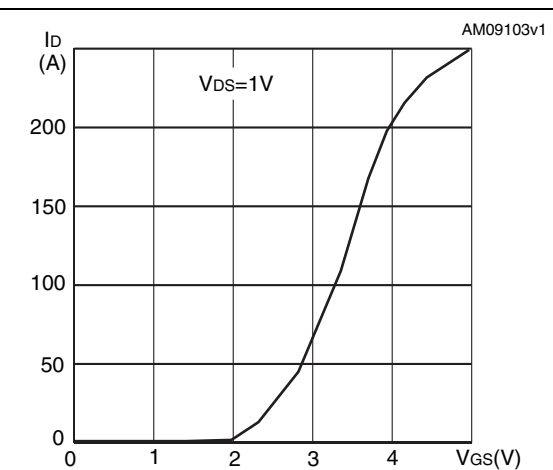


Figure 6. Normalized BVDS vs temperature

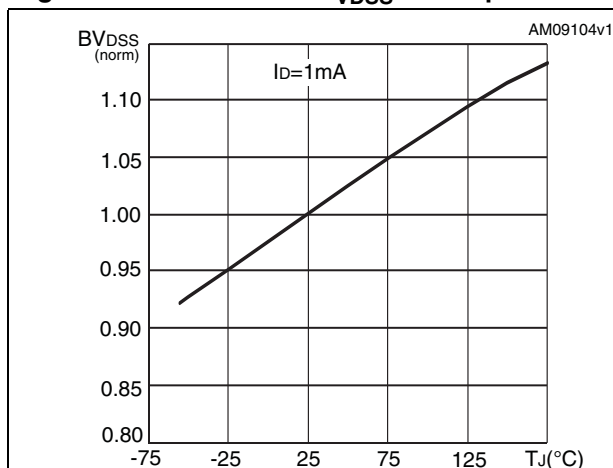


Figure 7. Static drain-source on resistance

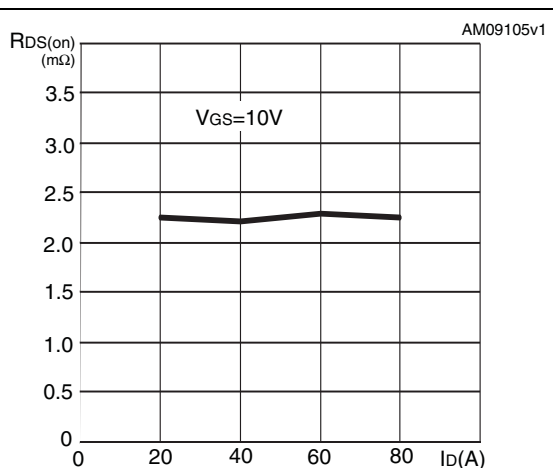


Figure 8. Gate charge vs gate-source voltage

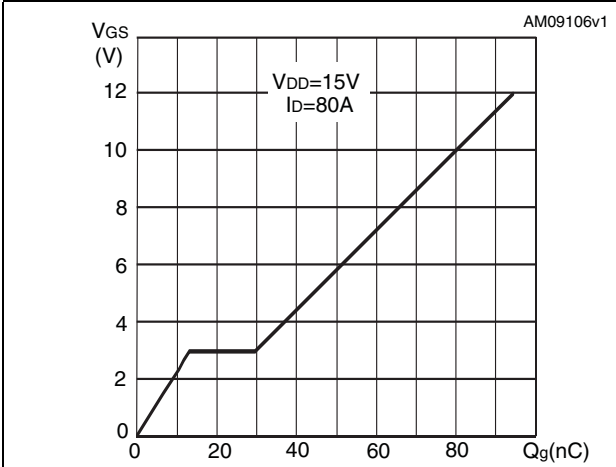


Figure 9. Capacitance variations

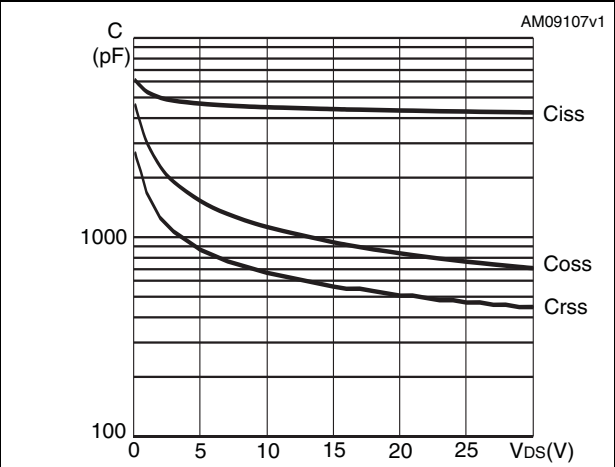


Figure 10. Normalized gate threshold voltage vs temperature

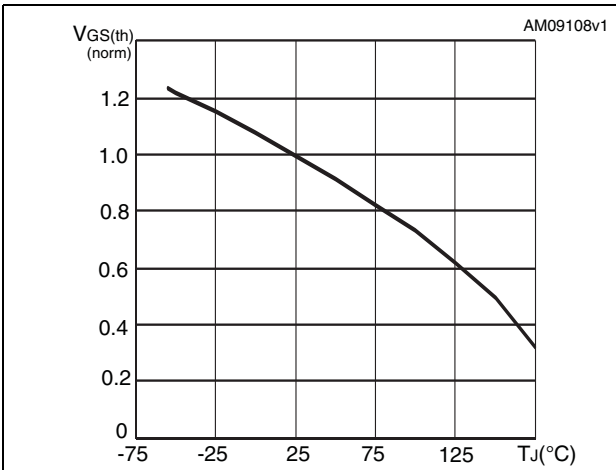


Figure 11. Normalized on resistance vs temperature

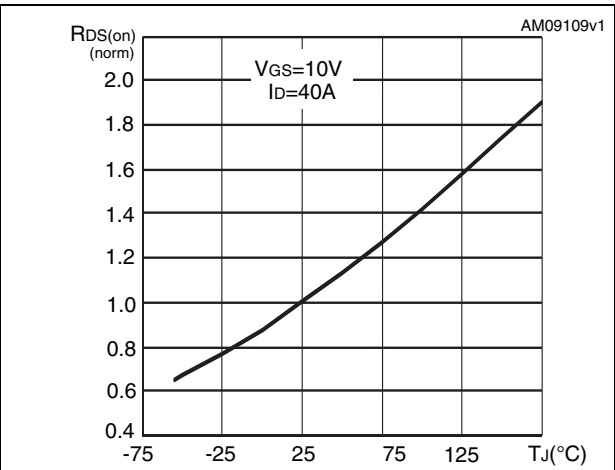
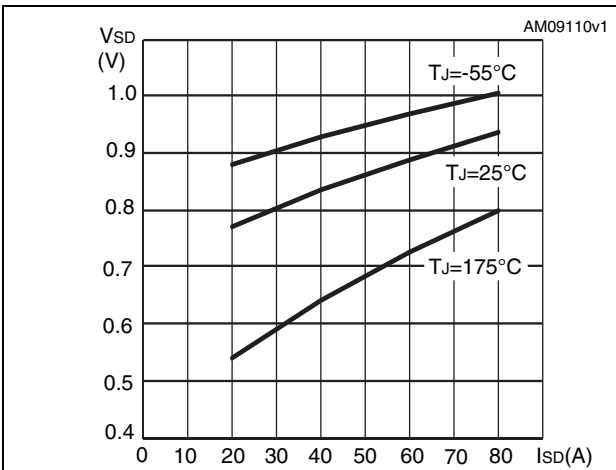


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load



Figure 14. Gate charge test circuit



Figure 15. Test circuit for inductive load switching and diode recovery times

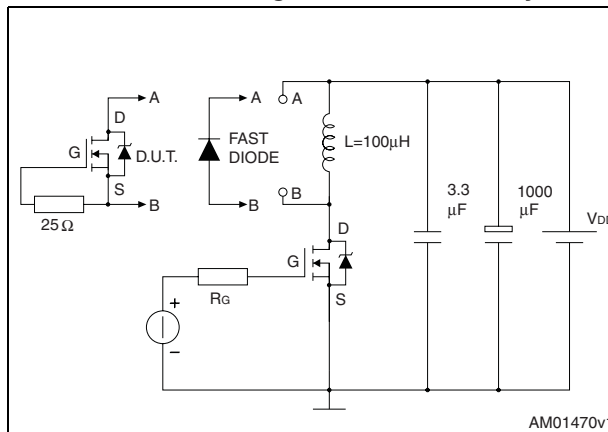


Figure 16. Unclamped Inductive load test circuit



Figure 17. Unclamped inductive waveform

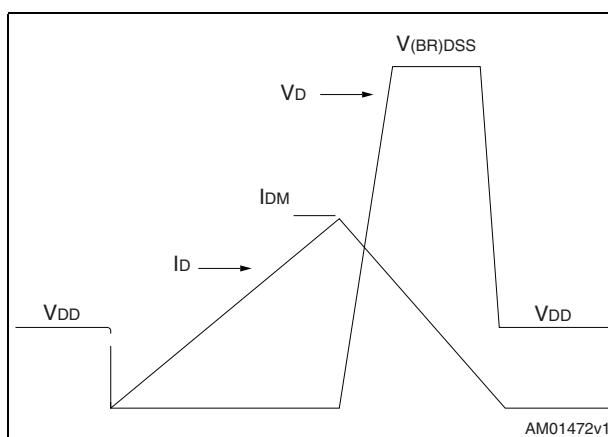
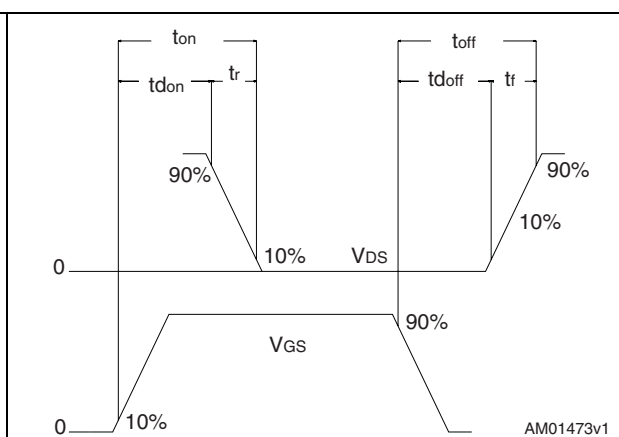


Figure 18. Switching time waveform

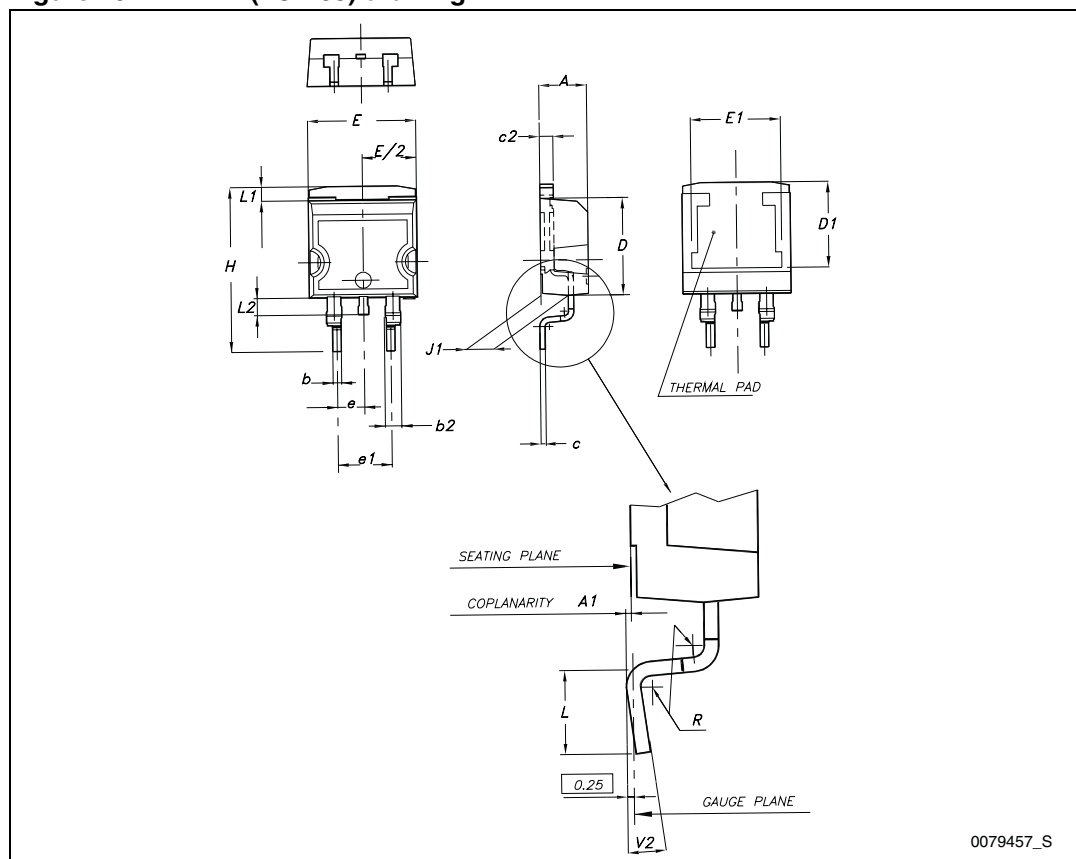
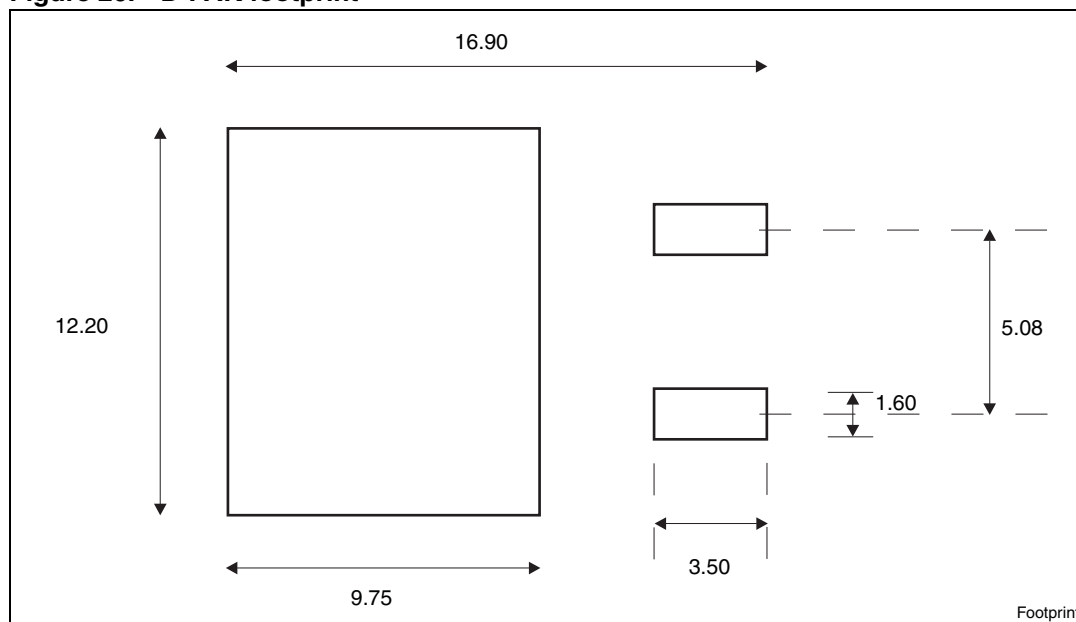


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 19. D²PAK (TO-263) drawingFigure 20. D²PAK footprint^(a)

a. All dimension are in millimeters

Table 10. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		1.50
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 21. DPAK (TO-252) drawing

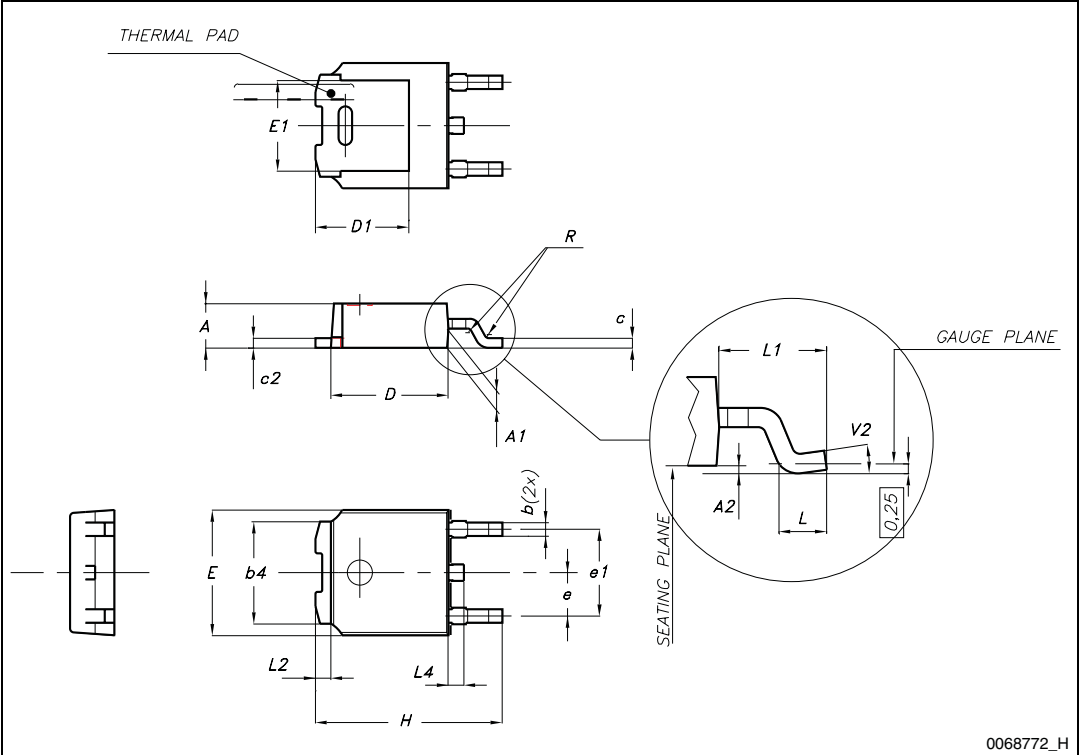
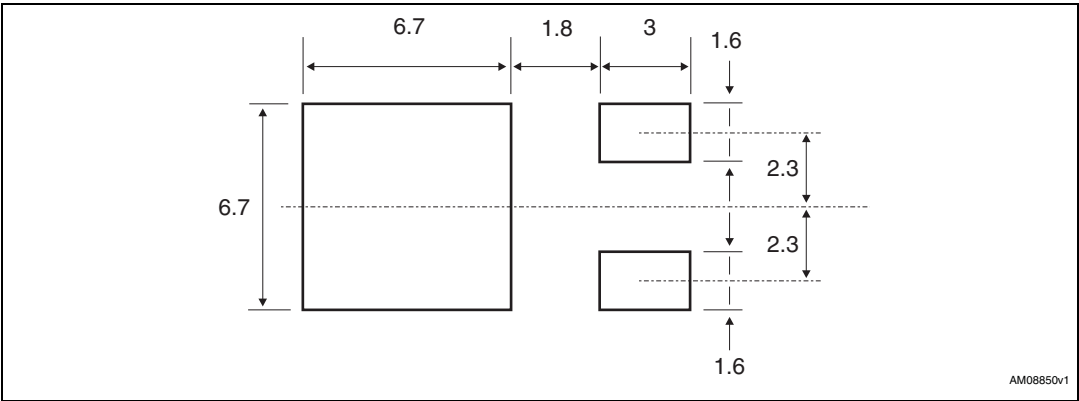


Figure 22. DPAK footprint^(b)



b. All dimension are in millimeters

5 Packaging mechanical data

Table 11. D²PAK (TO-263) tape and reel mechanical data

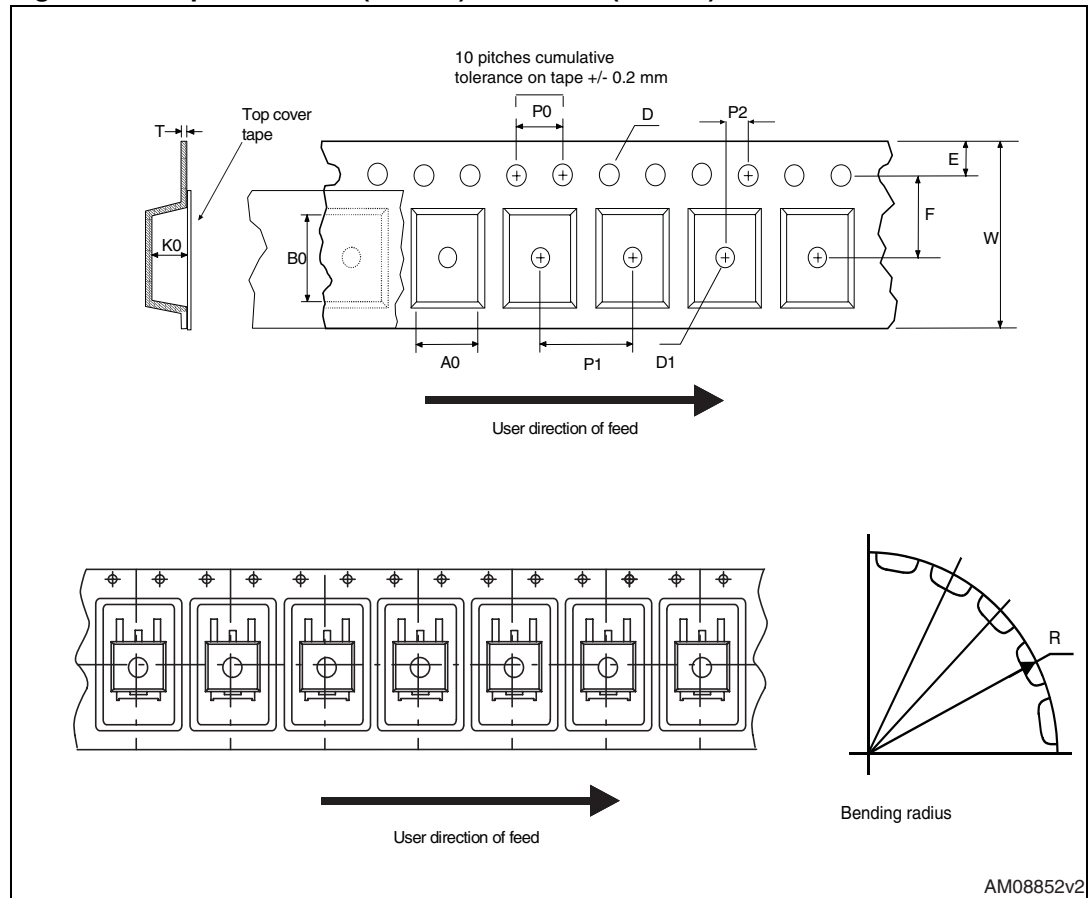
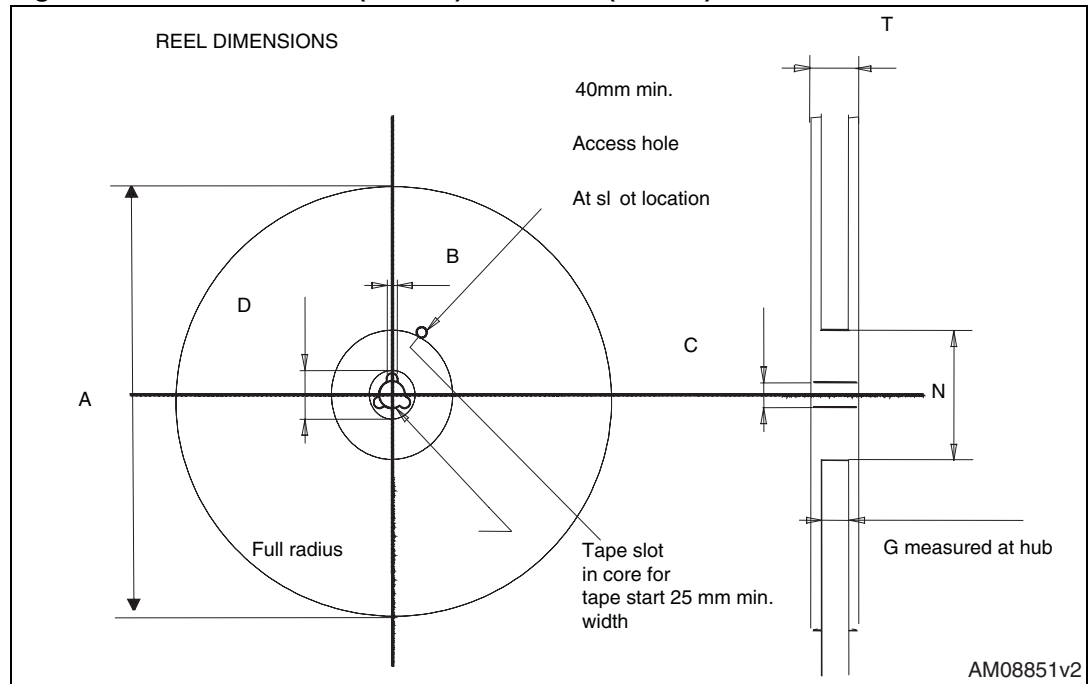
Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Table 12. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500

Table 12. DPAK (TO-252) tape and reel mechanical data (continued)

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 23. Tape for D²PAK (TO-263) and DPAK (TO-252)Figure 24. Reel for D²PAK (TO-263) and DPAK (TO-252)

6 Revision history

Table 13. Document revision history

Date	Revision	Changes
02-Sep-2010	1	First release.
12-Apr-2011	2	Document status promoted from preliminary data to datasheet.
27-Sep-2011	3	Updated Table 1: Device summary , Figure 2: Safe operating area and Section 4: Package mechanical data . Minor text changes.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2011 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com